



JST134V-800D 1A TRIAC

Rev.

/1

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	- -	MAX.	5	mA
				10	
V _{GT}		ALL	MAX.	1.3	V
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3K	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	- -	MAX.	10	mA
				20	
I _H	I _T =100mA		MAX.	7	mA
dV/dt	V _D =540V Gate Open T _j =110		MIN.	100	V/μs
(dV/dt) _c	(dI/dt) _c =1.8A/ms, T _j =110		MIN.	2.5	V/μs
t _{on}	I _G =20mA I _A =200mA I _R =20mA T _j =25		TYP.	2.5	μs
t _{off}				25	

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =5A t _p =380μs	T _j =25	1.55	V
V _{TO}	Threshold voltage	T _j =125	0.92	V
R _D	Dynamic resistance	T _j =125	107	m
I _{DRM}	V _D =V _{DRM} V _R =V _{RDM}	T _j =25	5	μA
I _{RDM}		T _j =125	0.35	mA

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	18	/W
R _{th(j-a)}	junction to ambient (AC)	150	/W

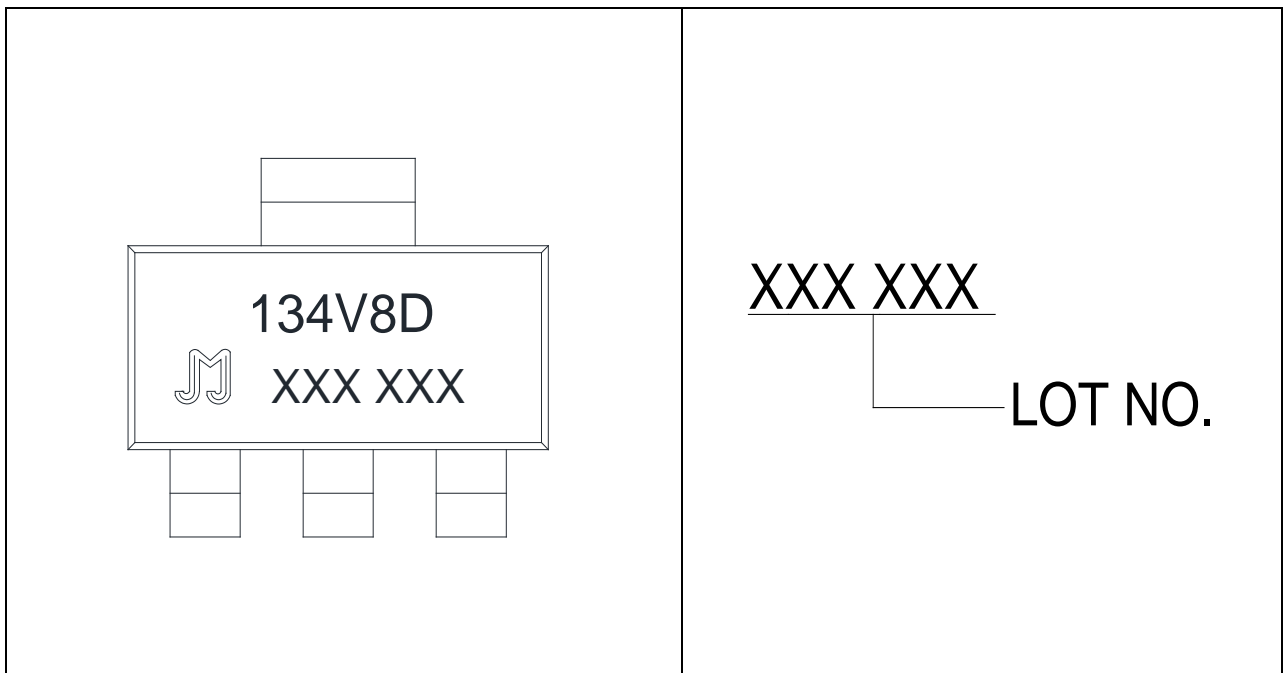
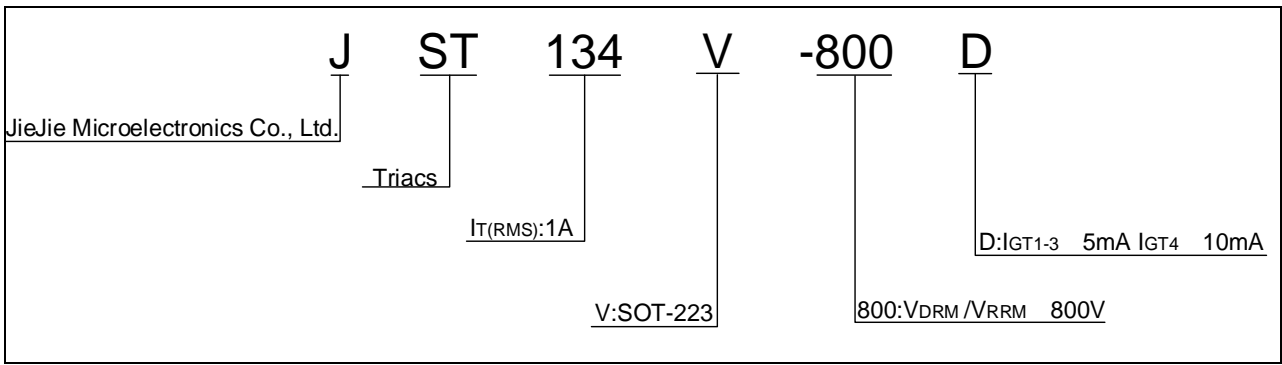


FIG.1 Maximum power dissipation versus RMS on-state current

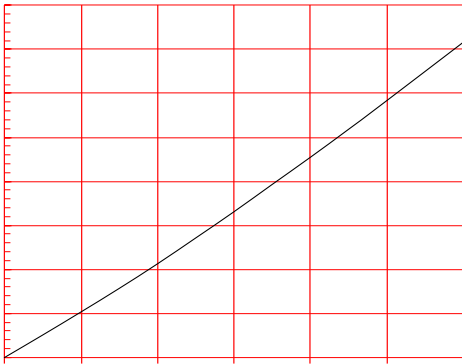


FIG.2: RMS on-state current versus case temperature

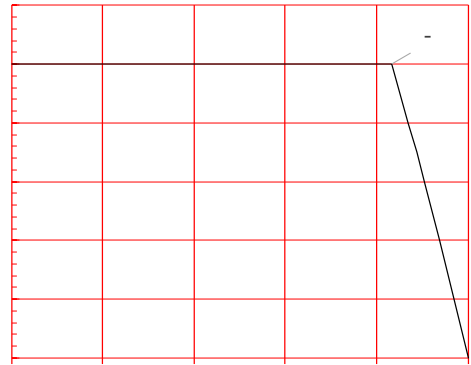


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35μm) (full cycle)

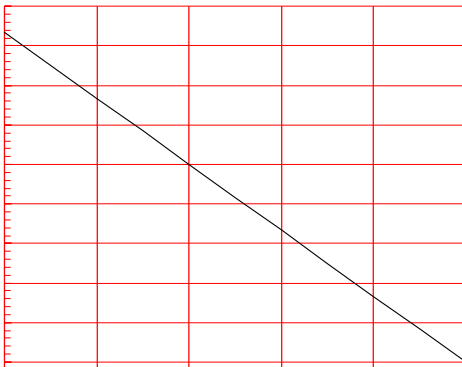


FIG.4: Surge peak on-state current versus number of cycles

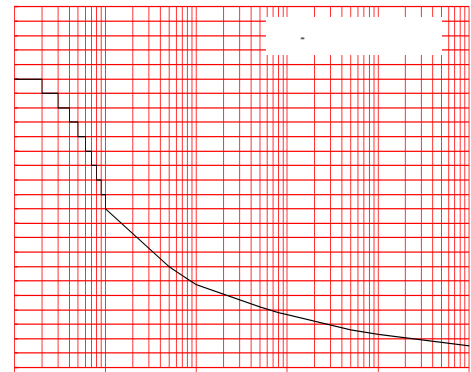


FIG.5: On-state characteristics

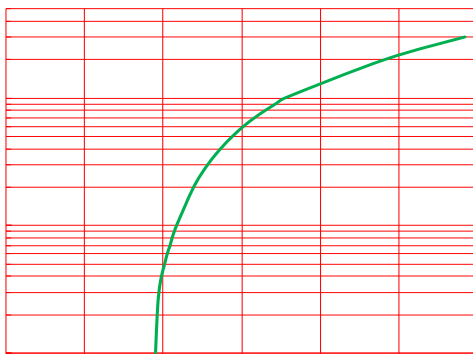


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (- - : $dl/dt < 50\text{A}/\mu\text{s}$; : $dl/dt < 30\text{A}/\mu\text{s}$)

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

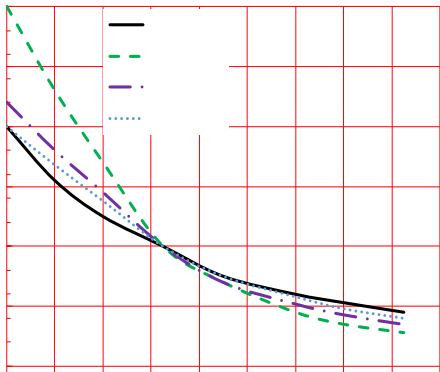
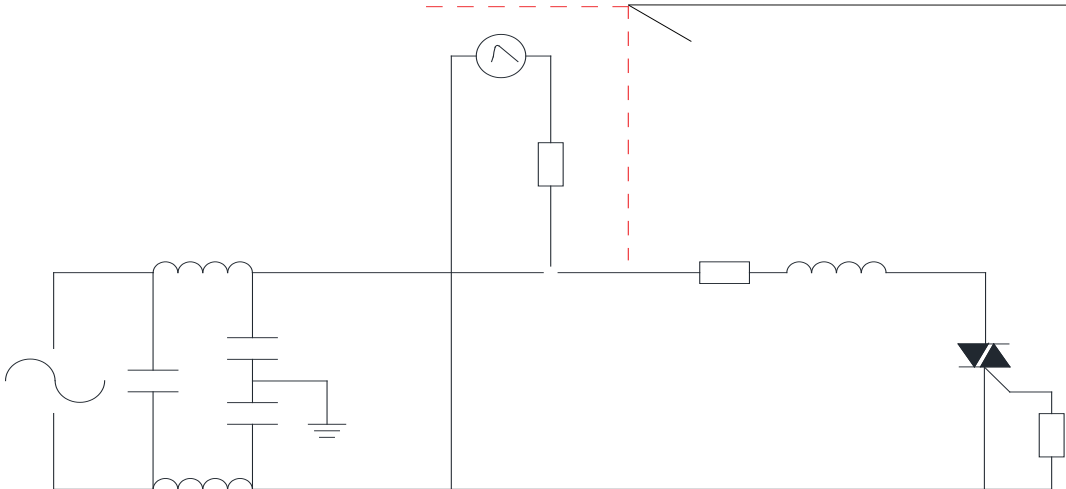


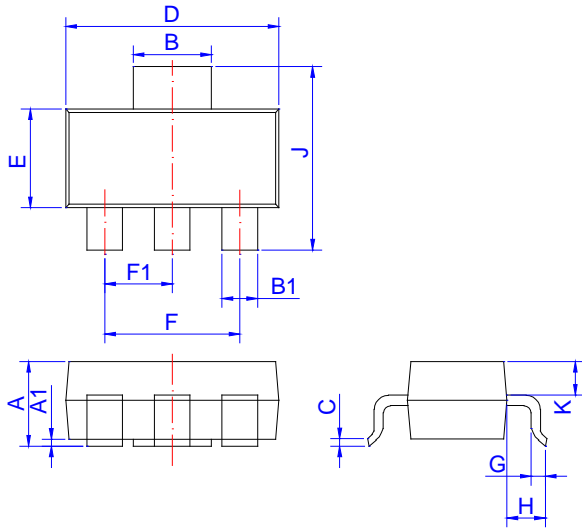
FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



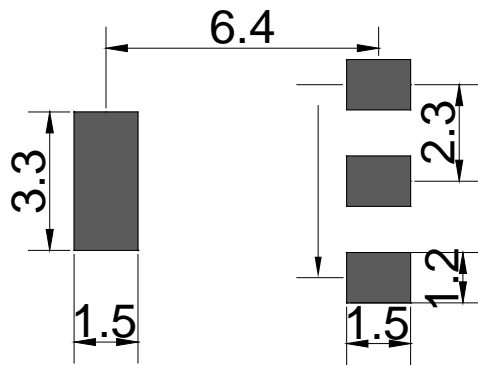
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		H- I- J	K			
JST134V-800D	800	5	10	SOT-223	4,000	Tape & Reel

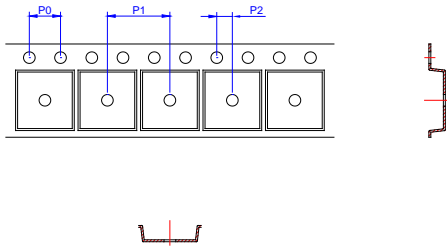
Document Revision History

Date	Revision	
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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F	4.4		4.8	0.173		0.189
F1	2.2		2.4	0.087		0.094
G	0.5		1.0	0.020		0.039
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K	0.8	0.9	1.0	0.031	0.035	0.039





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-		12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0		1.55	1.60		0.061	0.063
D1		-	-			
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

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